BC846ALT1G Series

General Purpose Transistors

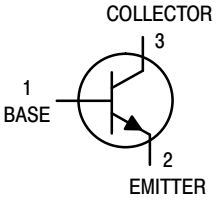
NPN Silicon

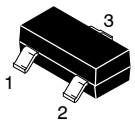
ON Semiconductor®

http://onsemi.com

Features

- Moisture Sensitivity Level: 1
- ESD Rating – Human Body Model: >4000 V
  – Machine Model: >400 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant





SOT–23
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847, BC850 BC848, BC849	V_{CEO}	 65 45 30	Vdc
Collector–Base Voltage BC846 BC847, BC850 BC848, BC849	V_{CBO}	 80 50 30	Vdc
Emitter–Base Voltage BC846 BC847, BC850 BC848, BC849	V_{EBO}	 6.0 6.0 5.0	Vdc
Collector Current – Continuous	I_C	100	mAdc

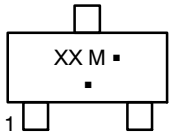
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C

1. FR–5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in 99.5% alumina.

MARKING DIAGRAM



XX = Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I_C = 10 mA)	BC846A,B	$V_{(BR)CEO}$	65	–	–	V
	BC847A,B,C, BC850B,C		45	–	–	
	BC848A,B,C, BC849B,C		30	–	–	
Collector – Emitter Breakdown Voltage (I_C = 10 μA, V_{EB} = 0)	BC846A,B	$V_{(BR)CES}$	80	–	–	V
	BC847A,B,C BC850B,C		50	–	–	
	BC848A,B,C, BC849B,C		30	–	–	
Collector – Base Breakdown Voltage (I_C = 10 μA)	BC846A,B	$V_{(BR)CBO}$	80	–	–	V
	BC847A,B,C, BC850B,C		50	–	–	
	BC848A,B,C, BC849B,C		30	–	–	
Emitter – Base Breakdown Voltage (I_E = 1.0 μA)	BC846A,B	$V_{(BR)EBO}$	6.0	–	–	V
	BC847A,B,C, BC850B,C		6.0	–	–	
	BC848A,B,C, BC849B,C		5.0	–	–	
Collector Cutoff Current (V_{CB} = 30 V)		I_{CBO}	–	–	15	nA
(V_{CB} = 30 V, T_A = 150°C)			–	–	5.0	μA
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 μA, V_{CE} = 5.0 V)	BC846A, BC847A, BC848A	h_{FE}	–	90	–	–
	BC846B, BC847B, BC848B		–	150	–	
	BC847C, BC848C		–	270	–	
(I_C = 2.0 mA, V_{CE} = 5.0 V)	BC846A, BC847A, BC848A		110	180	220	
	BC846B, BC847B, BC848B, BC849B, BC850B		200	290	450	
	BC847C, BC848C, BC849C, BC850C		420	520	800	
Collector – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA)		$V_{CE(sat)}$	–	–	0.25	V
(I_C = 100 mA, I_B = 5.0 mA)			–	–	0.6	
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA)		$V_{BE(sat)}$	–	0.7	–	V
(I_C = 100 mA, I_B = 5.0 mA)			–	0.9	–	
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V)		$V_{BE(on)}$	580	660	700	mV
(I_C = 10 mA, V_{CE} = 5.0 V)			–	–	770	
SMALL–SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	100	–	–	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)		C_{obo}	–	–	4.5	pF
Noise Figure (I_C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF				dB
	BC846A,B, BC847A,B,C, BC848A,B,C		–	–	10	
	BC849B,C, BC850B,C		–	–	4.0	

BC847, BC848, BC849, BC850

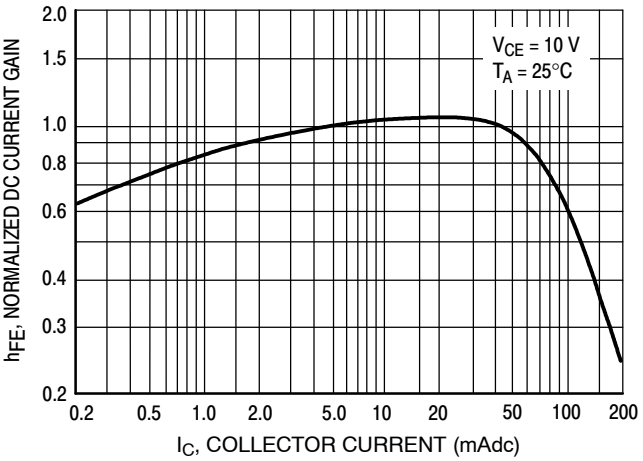


Figure 1. Normalized DC Current Gain

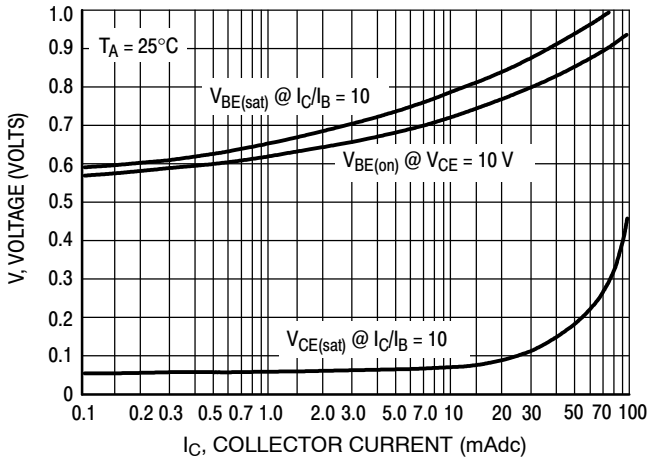


Figure 2. "Saturation" and "On" Voltages

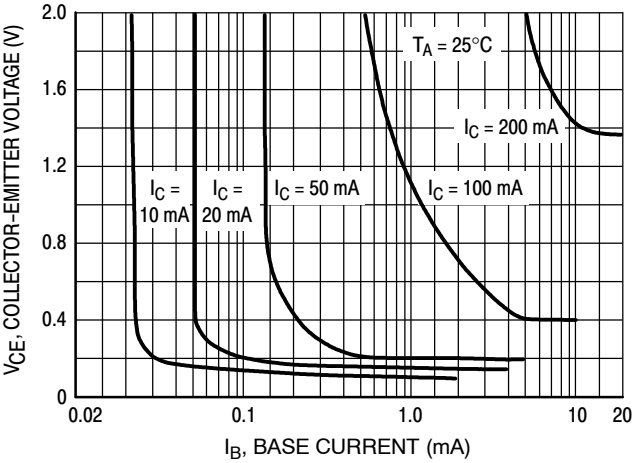


Figure 3. Collector Saturation Region

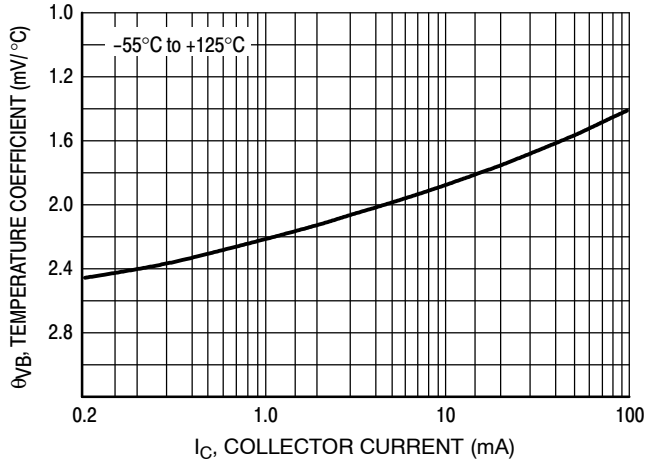


Figure 4. Base−Emitter Temperature Coefficient

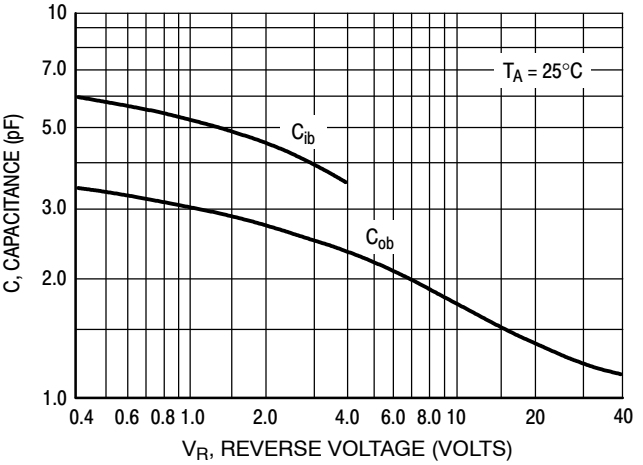


Figure 5. Capacitances

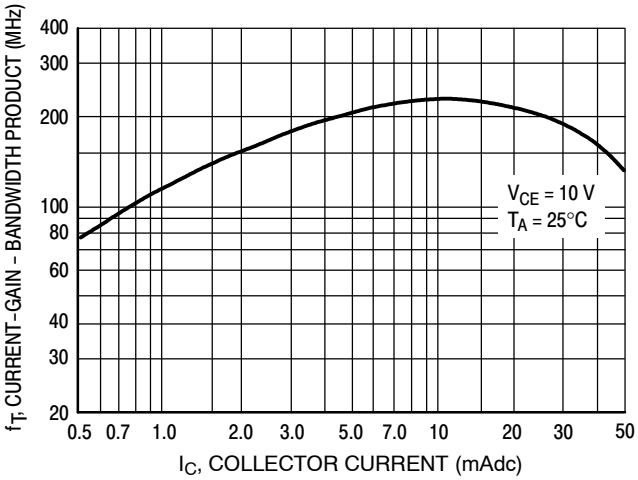


Figure 6. Current−Gain − Bandwidth Product

BC846

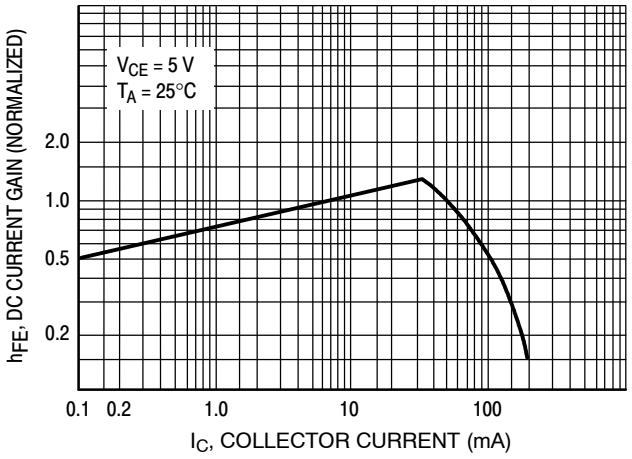


Figure 7. DC Current Gain

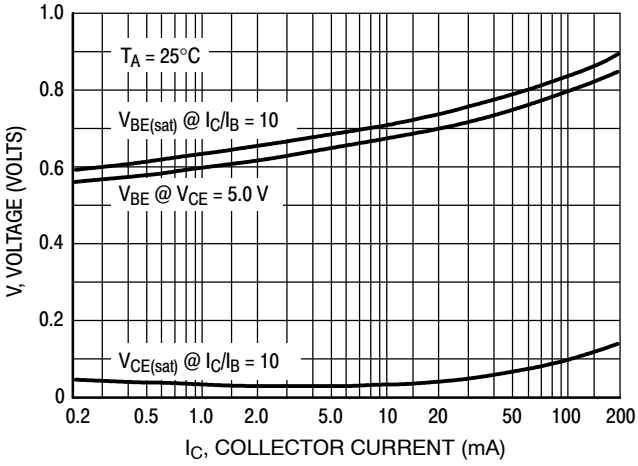


Figure 8. "On" Voltage

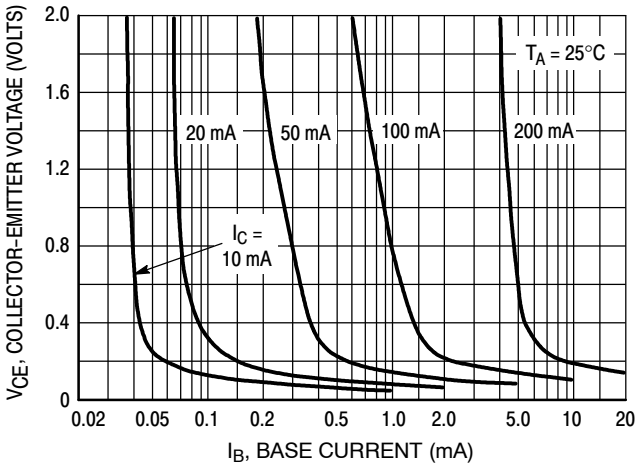


Figure 9. Collector Saturation Region

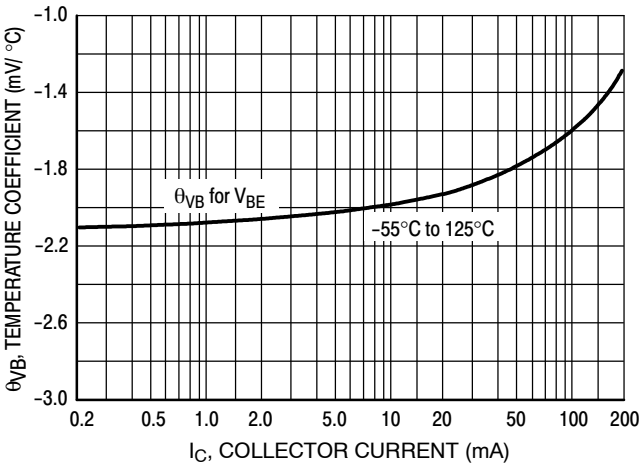


Figure 10. Base−Emitter Temperature Coefficient

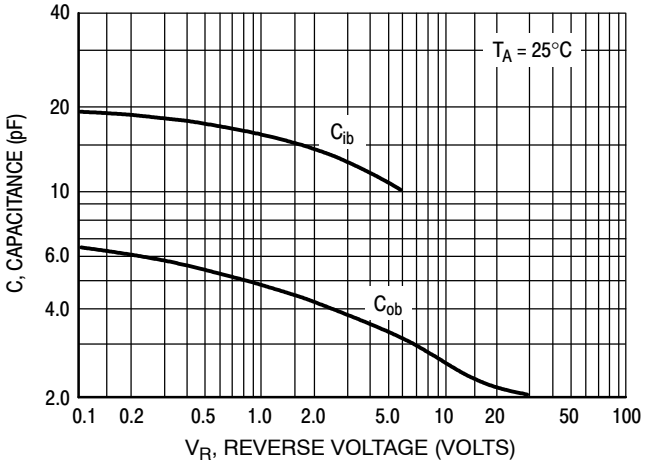


Figure 11. Capacitance

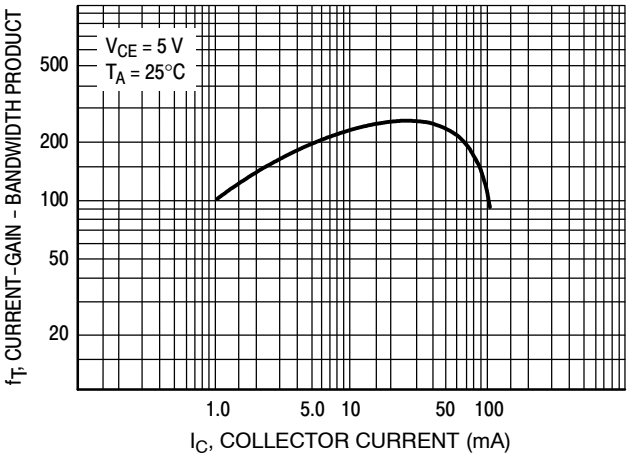


Figure 12. Current−Gain − Bandwidth Product

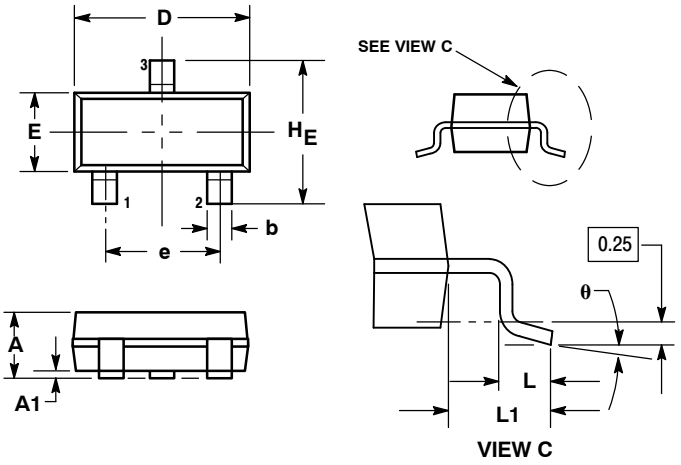
ORDERING INFORMATION

Device	Marking	Package	Shipping†
BC846ALT1G	1A	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC846ALT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC846BLT1G	1B	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC846BLT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC847ALT1G	1E	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC847ALT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC847BLT1G	1F	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC847BLT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC847CLT1G	1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC847CLT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC848ALT1G	1J	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC848BLT1G	1K	SOT−23 (Pb−Free)	
BC848BLT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC848CLT1G	1L	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC848CLT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC849BLT1G	2B	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC849BLT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC849CLT1G	2C	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC849CLT3G		SOT−23 (Pb−Free)	10,000 / Tape & Reel
BC850BLT1G	2F	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC850CLT1G	2G	SOT−23 (Pb−Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AN

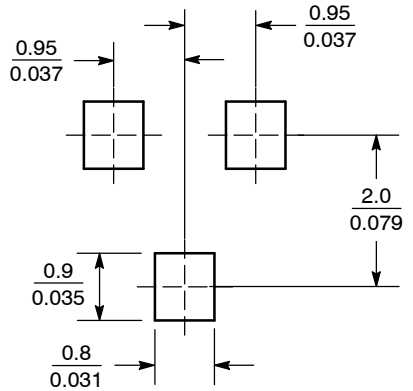


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01 THRU −07 AND −09 OBSOLETE, NEW STANDARD 318−08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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Japan Customer Focus Center
Phone: 81−3−5773−3850

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